Hyperfast Rectifier

30 A, 600 V

RHRG3060-F085

Description

The RHRG3060–F085 is a hyperfast diode with soft recovery characteristics (trr < 45 ns). It has half the recovery time of ultrafast diode and is of silicon nitride passivated ion–implanted epitaxial planar construction.

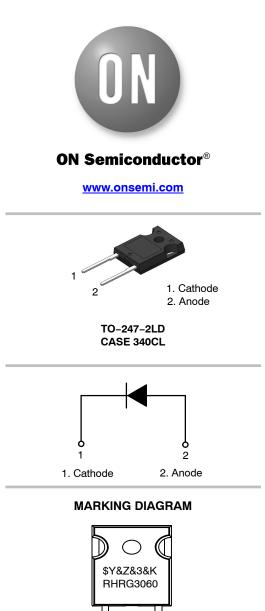
This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of automotive switching power supplies and other power switching automotive applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Features

- High Speed Switching ($t_{rr} = 45 \text{ ns}(\text{Typ.}) @ I_F = 30 \text{ A}$)
- Low Forward Voltage ($V_F = 1.64 \text{ V(Typ.)} @ I_F = 30 \text{ A}$)
- Avalanche Energy Rated
- AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free

Applications

- Switching Power Supply
- Power Switching Circuits
- Automotive and General Purpose



ORDERING INFORMATION

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RHRG3060

See detailed ordering and shipping information on page 2 of this data sheet.

= ON Semiconductor Logo

= Assembly Plant Code

= Specific Device Code

= Numeric Date Code

= Lot Code

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	600	V
Working Peak Reverse Voltage	V _{RWM}	600	V
DC Blocking Voltage	V _R	600	V
Average Rectified Forward Current ($T_C = 25^{\circ}C$)	I _{F(AV)}	30	А
Non-repetitive Peak Surge Current (Halfwave 1 Phase 50 Hz)		90	А
Avalanche Energy (1 A, 40 mH)		20	mJ
Operating Junction and Storage Temperature	$T_{J,}T_{STG}$	–55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Tube	Quantity
RHRG3060-F085	RHRG3060	TO-247-2LD	-	30

THERMAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Parameter		Value	Unit
Maximum Thermal Resistance, Junction to Case		0.66	°C/W
Maximum Thermal Resistance, Junction to Ambient		45	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

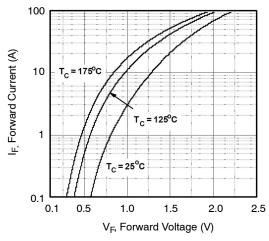
Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit
Instantaneous Reverse Current	I _R	V _R = 600 V	$T_C = 25^{\circ}C$	-	-	250	μA
			T _C = 175°C	-	-	1.5	mA
Instantaneous Forward Voltage (Note 1)	V _{FM}	I _F = 30 A	$T_C = 25^{\circ}C$	-	1.64	2.1	V
			T _C = 175°C	-	1.24	1.7	V
Reverse Recovery Time (Note 2)	t _{rr}	I_F = 1 A, di/dt = 200 A/µs, V_{CC} = 390 V	T _C = 25°C	-	24	40	ns
		I_F = 30 A, di/dt = 200 A/µs, V_{CC} = 390 V	$T_{C} = 25^{\circ}C$	-	33	45	ns
			T _C = 175°C	-	136	-	ns
Reverse Recovery Time	t _a	$I_{\rm F} = 30$ A, di/dt = 200 A/µs,	$T_C = 25^{\circ}C$	-	19	-	ns
	t _b	V _{CC} = 390 V		-	14	-	ns
Reverse Recovery Charge	Q _{rr}]		-	60	-	nC

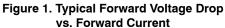
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse: Test Pulse Width = 300 μ s, Duty Cycle = 2%

2. Guaranteed by design.

TYPICAL PERFORMANCE CHARACTERISTICS





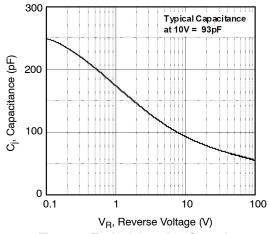


Figure 3. Typical Junction Capacitance

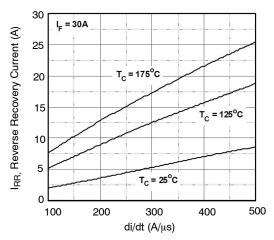


Figure 5. Typical Reverse Recovery Current vs. di/dt

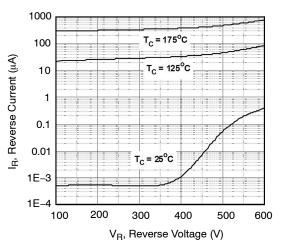


Figure 2. Typical Reverse Current vs. Reverse Voltage

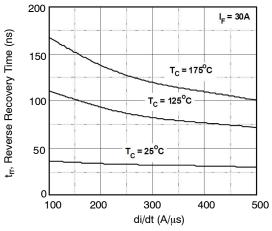


Figure 4. Typical Reverse Recovery Time vs. di/dt

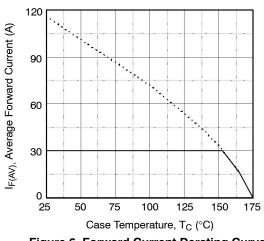


Figure 6. Forward Current Derating Curve

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

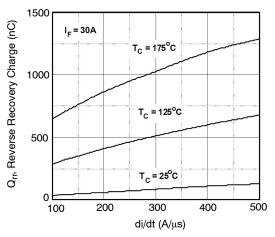


Figure 7. Reverse Recovery Charge

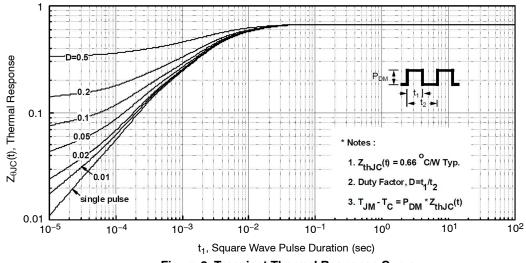
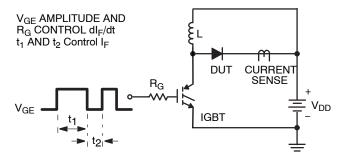


Figure 8. Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS





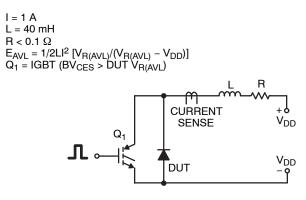


Figure 11. Avalanche Energy Test Circuit

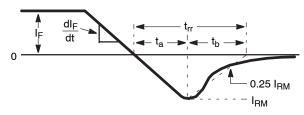


Figure 10. t_{rr} Waveforms and Definitions

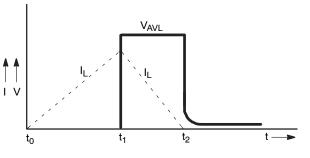


Figure 12. Avalanche Current and Voltage Waveforms

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MILLIMETERS

NOM

4.70

2.40

1.50

1.26

1.65

0.61

20.57

16.57

0.93

15.62

~

5.08

11.12

16.00

3.81

3.58

6.73

5.46

5.46

MAX

4.82

2.66

1.70

1.35

1.77

0.71

20.82

16.77

1.35

15.87

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5.20

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16.25

3.93

3.65

6.85

5.58

5.58

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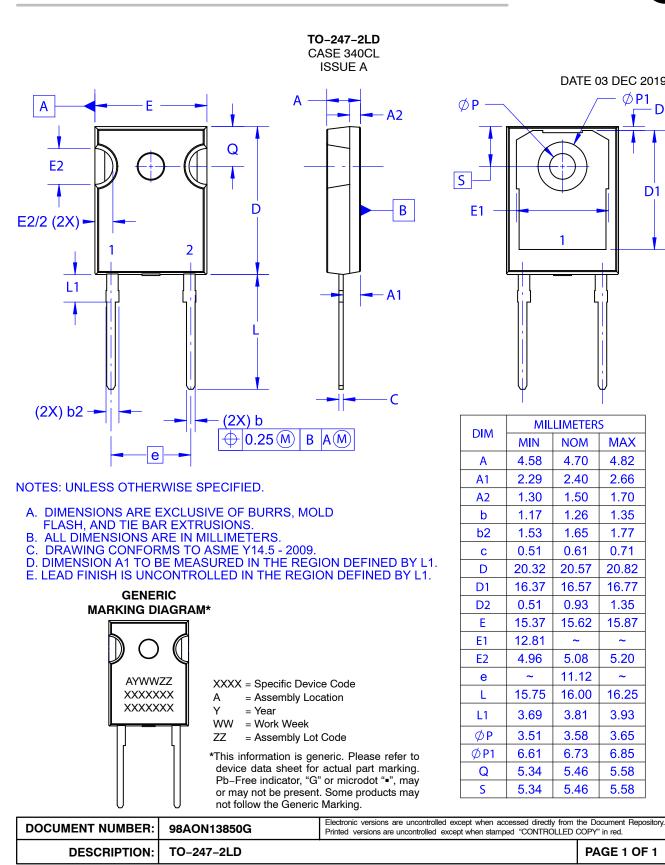
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